ALPHA & OMEGA SEMICONDUCTOR

AO4409
P-Channel Enhancement Mode Field Effect Transistor

General Description

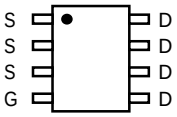
The AO4409/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications. *AO4409 and AO4409L are electrically identical.*
-RoHS Compliant
-AO4409L is Halogen Free

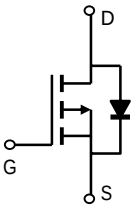
Features

V_{DS} (V) = -30V
I_D = -15 A (V_{GS} = -10V)
Max $R_{DS(ON)}$ < 7.5mΩ (V_{GS} = -10V)
Max $R_{DS(ON)}$ < 12mΩ (V_{GS} = -4.5V)

UIS Tested!
Rg, Ciss,Coss,Crss Tested

SOIC-8
Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [AF]	T_A=25°C	I_D	-15	A
	T_A=70°C		-12.8	
Pulsed Drain Current [B]		I_{DM}	-80	
Avalanche Current [G]		I_{AR}	30	A
Repetitive avalanche energy L=0.3mH [G]		E_{AR}	135	mJ
Power Dissipation [A]	T_A=25°C	P_D	3	W
	T_A=70°C		2.1	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	26	40	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		50	75	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	14	24	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-5	µA
		T_J=55°C			-25	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-1.4	-1.9	-2.7	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V	-80			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-15A		6.2	7.5	mΩ
		T_J=125°C		8.2	11.5	
		V_{GS}=-4.5V, I_D=-10A		9.5	12	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-15A	35	50		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.71	-1	V
I_S	Maximum Body-Diode Continuous Current				-5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz		5270	6400	pF
C_{oss}	Output Capacitance			945		pF
C_{rss}	Reverse Transfer Capacitance			745		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		2	3	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-15A		100	120	nC
Q_g(4.5V)	Gate Charge			51.5		nC
Q_{gs}	Gate Source Charge			14.5		nC
Q_{gd}	Gate Drain Charge			23		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=1Ω, R_{GEN}=3Ω		14		ns
t_r	Turn-On Rise Time			16.5		ns
$t_{D(off)}$	Turn-Off DelayTime			76.5		ns
t_f	Turn-Off Fall Time			37.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-15A, dI/dt=100A/µs		36.7	45	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-15A, dI/dt=100A/µs		28		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using <300µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

F. The current rating is based on the t ≤ 10s thermal resistance rating.

G. EAR and IAR ratings are based on low frequency and duty cycles such that Tj(start)=25C for each pulse.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

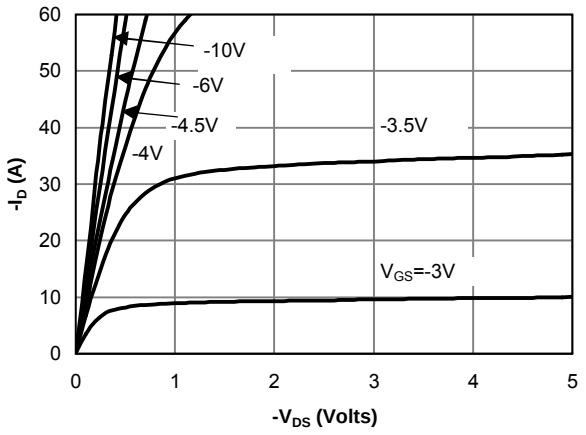

Fig 1: On-Region Characteristics

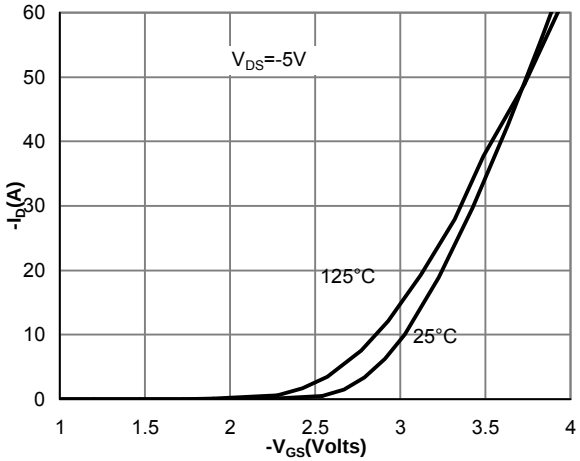

Figure 2: Transfer Characteristics

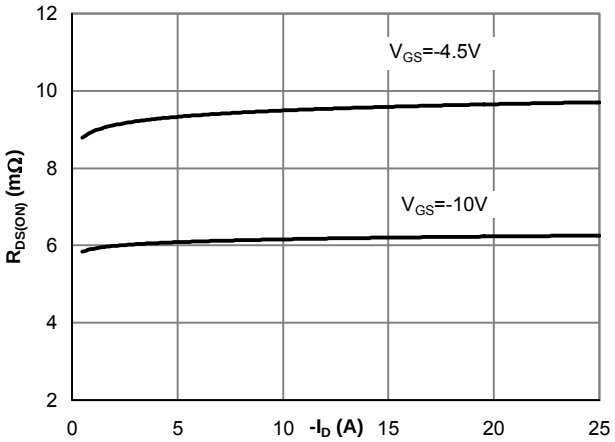

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

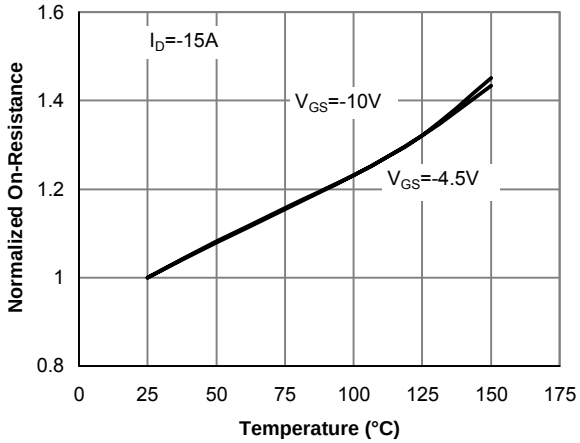

Figure 4: On-Resistance vs. Junction Temperature

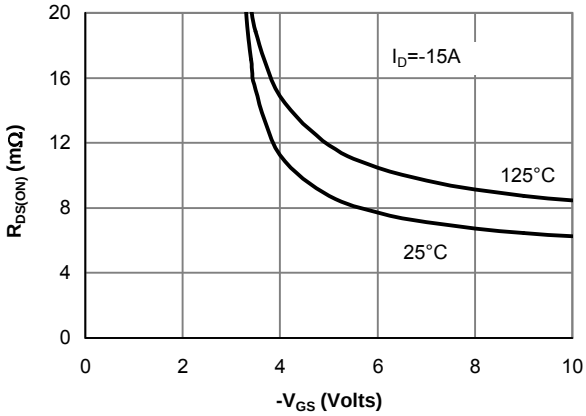

Figure 5: On-Resistance vs. Gate-Source Voltage

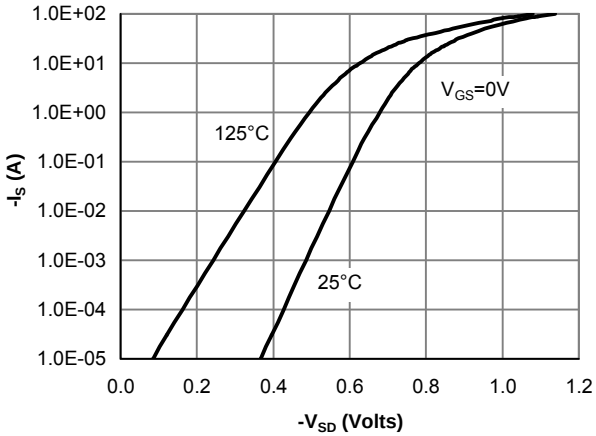

Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

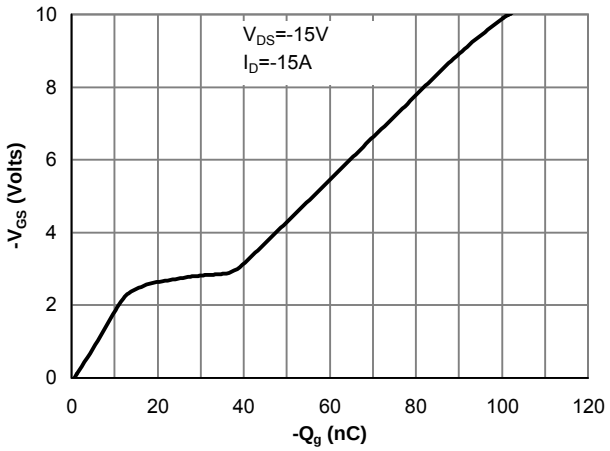

Figure 7: Gate-Charge Characteristics

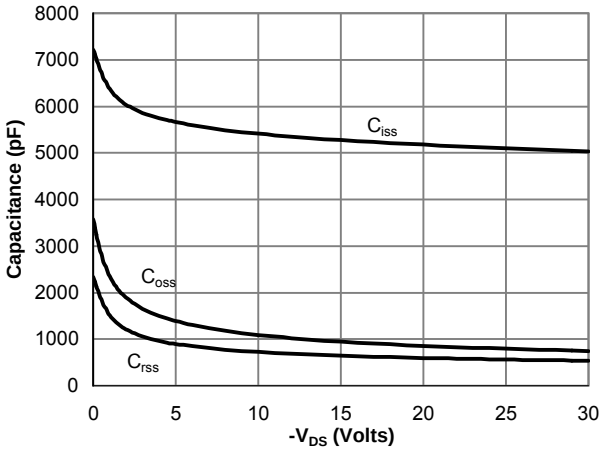

Figure 8: Capacitance Characteristics

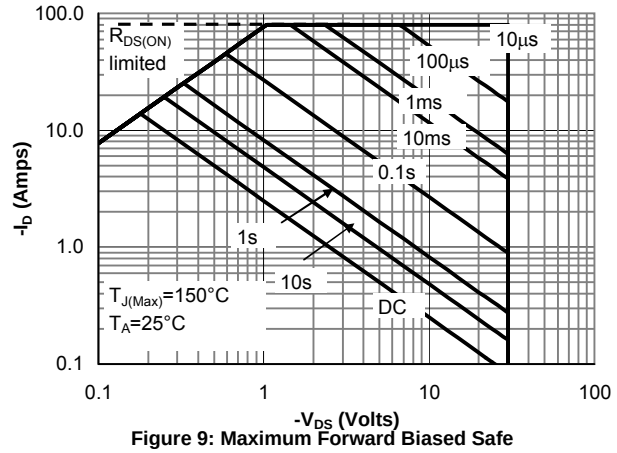

Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

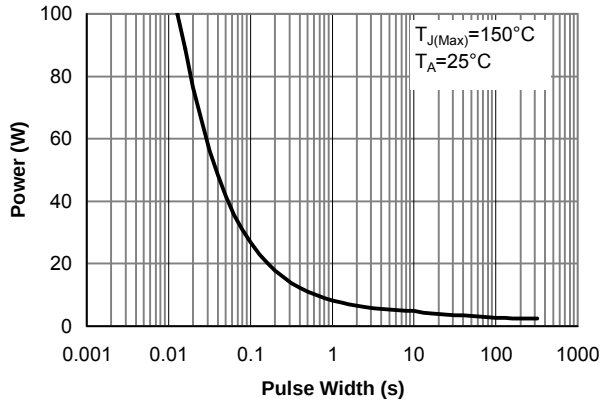

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

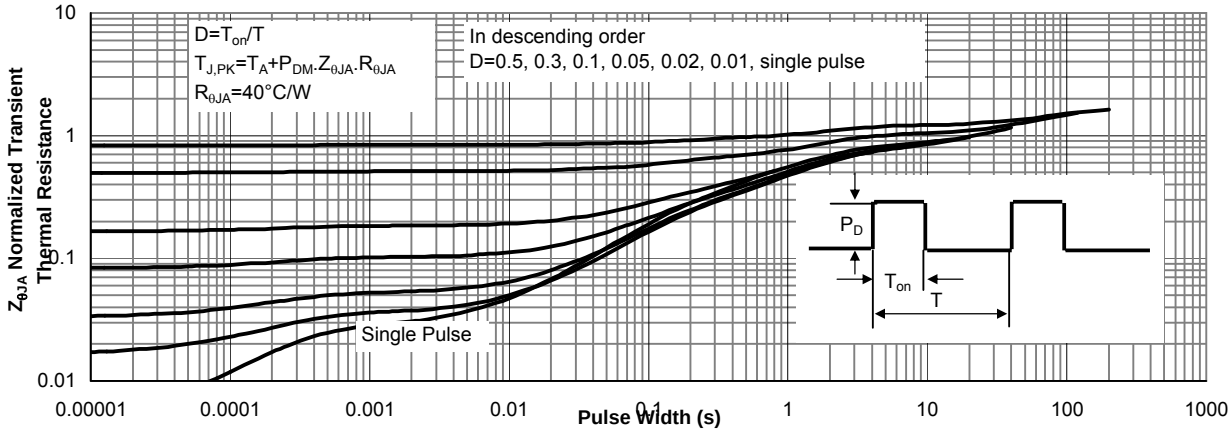

Figure 11: Normalized Maximum Transient Thermal Impedance